

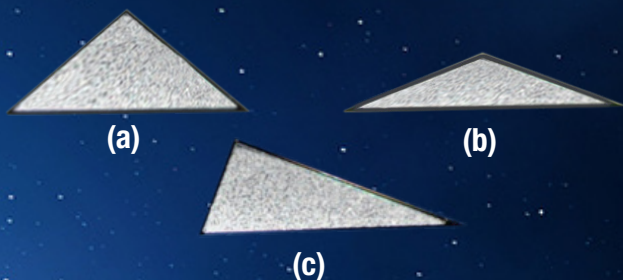
**The World Leader in  
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## SILICON BYPASS DIODES

### Three Form Factors for SolAero Silicon Bypass Diodes



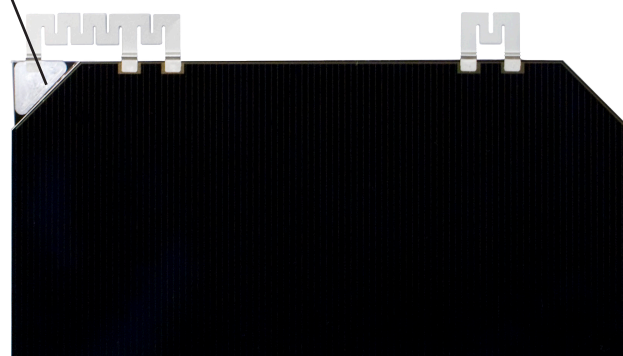
SolAero's Silicon Bypass Diodes are welded to the corner of SolAero Space Solar Cells and allow current to safely bypass cells in a string as required during string operation.

Diode Form Factor	Area (cm <sup>2</sup> )	Average	
		Mass (mg)	Thickness (μm)
a	0.32	15	160
b	0.32	15	160
c	0.45	21	160

## FEATURES & CHARACTERISTICS

- Small size and light weight
- Low leakage current under reverse bias
- Low series resistance under forward bias
- Qualified by an extensive series of reliability tests
- The diode assemblies also include welded back-side interconnects

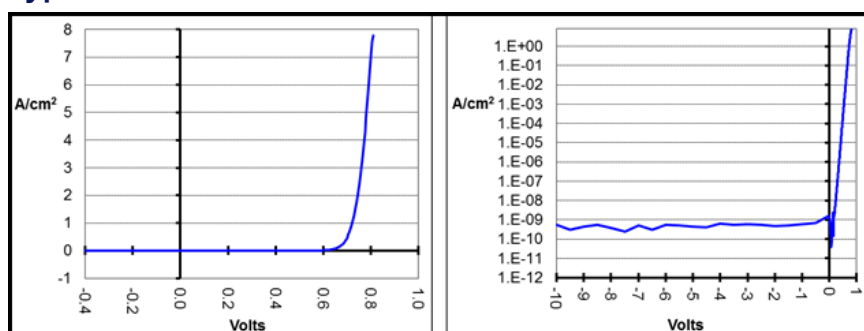
Corner-mounted Silicon Bypass Diode (shown interconnected with a SolAero Solar Cell to make a CIC).



## Electrical Specifications and Performance of ~0.32cm<sup>2</sup> Diodes (Dark IV Testing)

Temperature	Test	Condition	Max for Condition	Typical for Condition
23°C	Reverse Leakage Current	V <sub>r</sub> = 50 V	1.0 mA	<5E-9 A
		V <sub>r</sub> = 2.5 V	0.05 mA	<5E-9 A
	Forward Voltage	I <sub>f</sub> = 1.2 A	0.85 V	0.77 V
		I <sub>f</sub> = 2 A	1.1 V	0.81 V
-180°C	Forward Voltage	I <sub>f</sub> = 1.2 A	1.2 V	1.08 V
150°C	Reverse Leakage Current	V <sub>r</sub> = 2.5 V	1.2 mA	7E-7 A
	Forward Voltage	I <sub>f</sub> = 1.2 A	0.7 V	0.57 V

### Typical Diode Dark JV Curve at 22°C



### Mechanical Performance (Average Weld Pull Strength)

- Interconnect pulled at 0° angle from diode front contact: >1500 gf
- Interconnect pulled at 45° angle from diode front contact: 775 gf
- Interconnect pulled at 0° angle from diode back contact: >3500 gf
- Interconnect pulled at 45° angle from diode front contact: >790 gf

Note: Back contact pull tests are done one interconnect at a time. The pull strengths of the five weld system will be greater than those shown above.

### Qualification Testing Successfully Done on Silicon Bypass Diode

Name of Test	Description of Test
Electrical Cycling	100,000 Cycles at 150°C, alternating between forward current of 1.2 A and reverse bias of 2.5 V
Electron Irradiation	Exposure to irradiation levels of 5E13, 3E14, 5E14, 1E15 and 3E15 e/cm <sup>2</sup> (1 MeV electrons)
Forward Bias Life Test	1000 hours forward biased at 2.0 A at T=220°C
Gamma Radiation	Exposure to 120 Mrad Gamma radiation while biased to 2.30 V reverse bias
Human Body Model ESD	Exposure to 4,000 V electrostatic discharge, forward and reverse polarity
Humidity Exposure	720 hours at T <sub>c</sub> = 65°C and a relative humidity of 95%
Reverse Bias Life Test (HTRB)	1000 hours reverse biased to -50 V at T=150°C
Thermal Cycling	1980 thermal cycles from T <sub>c</sub> = -180°C to T <sub>c</sub> = +150°C
Thermal Shock	5 cycles of -180°C to +180°C by liquid-to-air immersion

